The RF Line NPN Silicon RF Power Transistor

Designed for 12.5 Volt UHF large—signal amplifier applications in industrial and commercial FM equipment operating to 520 MHz.

- Guaranteed 440, 470, 512 MHz 12.5 Volt Characteristics
 Output Power = 50 Watts
 Minimum Gain = 5.2 dB @ 440, 470 MHz
 Efficiency = 55% @ 440, 470 MHz
 IRL = 10 dB
- Characterized with Series Equivalent Large—Signal Impedance Parameters from 400 to 520 MHz
- Built-In Matching Network for Broadband Operation
- Triple Ion Implanted for More Consistent Characteristics
- Implanted Emitter Ballast Resistors
- Silicon Nitride Passivated
- 100% Tested for Load Mismatch Stress at all Phase Angles with 20:1 VSWR @ 15.5 Vdc, 2.0 dB Overdrive
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF650

50 W, 512 MHz RF POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|------------------|-------------|---------------|
| Collector–Emitter Voltage | VCEO | 16.5 | Vdc |
| Collector–Emitter Voltage | VCES | 38 | Vdc |
| Emitter–Base Voltage | V _{EBO} | 4.0 | Vdc |
| Collector Current — Continuous | lc | 12 | Adc |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 135 0.77 | Watts W/°C |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |
| Operating Junction Temperature | TJ | 200 | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--------------------------------------|-----------------|-----|------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.3 | °C/W |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|-----------------------|------|-----|-----|------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Emitter Breakdown Voltage (I _C = 50 mAdc, I _B = 0) | V _(BR) CEO | 16.5 | _ | _ | Vdc |
| Collector–Emitter Breakdown Voltage (I _C = 50 mAdc, V _{BE} = 0) | V(BR)CES | 38 | _ | _ | Vdc |
| Emitter–Base Breakdown Voltage (I _E = 10 mAdc, I _C = 0) | V(BR)EBO | 4.0 | _ | _ | Vdc |
| Collector Cutoff Current ($V_{CE} = 15 \text{ Vdc}$, $V_{BE} = 0$, $T_{C} = 25^{\circ}C$) | ICES | | _ | 5.0 | mAdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc) | hFE | 20 | 70 | 120 | _ |
| DYNAMIC CHARACTERISTICS | | | | | |
| Output Capacitance (V _{CB} = 12.5 Vdc, I _E = 0, f = 1.0 MHz) | C _{ob} | _ | 135 | 170 | pF |

(continued)

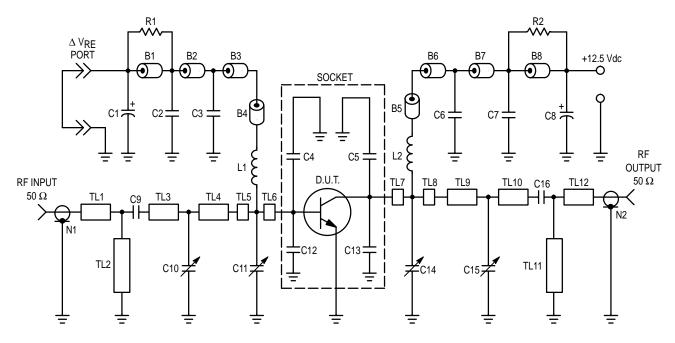


ELECTRICAL CHARACTERISTICS — **continued** (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|-----------------|--------------------------------|-----|-----|------|
| FUNCTIONAL TESTS (In Motorola Test Fixture. See Figure 1.) | | | | | |
| Common–Emitter Amplifier Power Gain (V _{CC} = 12.5 Vdc, P _{Out} = 50 W, f = 440, 470 MHz) | G _{pe} | 5.2 | 6.1 | _ | dB |
| Common–Emitter Amplifier Power Gain (V _{CC} = 12.5 Vdc, P _{out} = 50 W, f = 512 MHz) | G _{pe} | 5.0 | 5.9 | _ | dB |
| Input Return Loss (V _{CC} = 12.5 Vdc, P _{Out} = 50 W, f = 440, 470, 512 MHz) | IRL | 10 | 15 | _ | dB |
| Collector Efficiency (V _{CC} = 12.5 Vdc, P _{out} = 50 W, f = 440, 470 MHz) | η | 55 | 65 | _ | % |
| Collector Efficiency (V _{CC} = 12.5 Vdc, P _{out} = 50 W, f = 512 MHz) | _ | 50 | 60 | _ | % |
| Output Mismatch Stress (V _{CC} = 15.5 V, 2.0 dB Overdrive, f = 470 MHz, VSWR = 20:1, All Phase Angles) (1) | ψ (2) | No Degradation in Output Power | | | |

NOTES:

- 1. Pin = 2.0 dB above drive requirement for 50 W output at 12.5 Vdc.
- 2. ψ = Mismatch stress factor the electrical criterion established to verify the device resistance to load mismatch failure. The mismatch stress test is accomplished in the standard test fixture (Figure 1) terminated in a 20:1 minimum load mismatch at all phase angles.



B1, B8 — Ferrite Bead Ferroxcube VK200 20-4B

B2, B3, B4, B5, B6, B7 — Ferrite Bead Ferroxcube #56-590-3B

C1, C8 — 10 µF, 25 V, 25%, Electrolytic, ECS TE-1204

C2, C7 — 1000 pF, Chip Cap, 5%, ATC 100B102JC50

C3, C6 — 91 pF, 5%, Mica, SAHA 3HS0006-91

C4, C5, C12, C13 — 36 pF, 5%, SAHA 3HS0006-36

C9, C16 — 220 pF, Chip Cap, 5%, ATC 100B221JC200

C10, C11, C15 — 0.8-10 pF, Variable, Johanson JMC501 PG26J200

C14 — 1.0-20 pF, Variable, Johanson JMC5501 PG26J200

L1, L2 — 3 Turns, 18 AWG, 0.19" ID — Total Length 3.5"

N1, N2 — N Coaxial Conn., Omni-Spectra 3052-1648-10

R1, R2 — 10 Ohm, 10%, 1.0 W, Carbon, RCA 831010

TL1, TL12 — $Z_0 = 50 \text{ Ohm}$

TL2 — See Photomaster

TL3 — See Photomaster

TL4 — See Photomaster

TL5 — See Photomaster

TL6 — See Photomaster

TL7 — See Photomaster

TL8 — See Photomaster

TL9 — See Photomaster

TL10 — See Photomaster

TL11 — See Photomaster

Transmission Line Boards: 1/16" Glass-Teflon

Keene GX-0600-55-22 2 oz. Cu Clad Both Sides

 $\varepsilon_{\rm r} = 2.55$

Bias Boards: 1/16" G10 or Equivalent

2 oz. Cu Clad Double Sided

Figure 1. 440 to 512 MHz Broadband Test Circuit Schematic

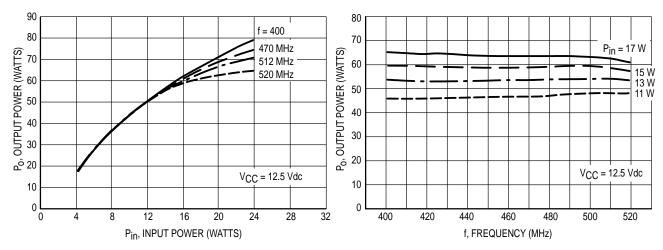


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Frequency

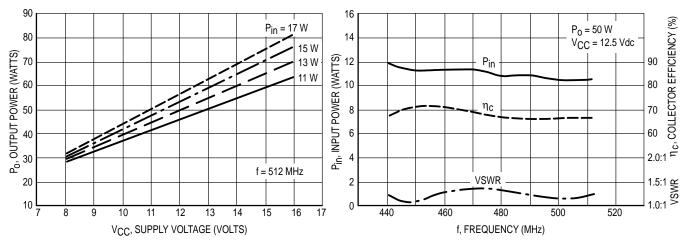
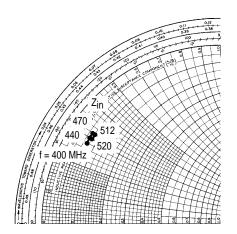


Figure 4. Output Power versus Supply Voltage

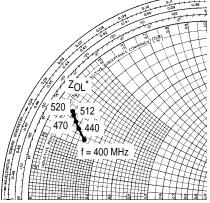
Figure 5. Broadband Performance for $P_0 = 50 \text{ W}$



 $P_{OUT} = 50 \text{ W}, V_{CC} = 12.5 \text{ Vdc}$ TUNED FOR MAXIMUM $GAIN AT P_0 = 50 \text{ W}$

| f | Z _{in} | Z _{OL} * |
|-------|-----------------|-------------------|
| (MHz) | Ω | Ω |
| 400 | 0.7 + j2.8 | 1.4 + j2.3 |
| 440 | 0.7 + j3.2 | 1.1 + j2.6 |
| 470 | 0.8 + j3.3 | 0.8 + j2.7 |
| 512 | 0.8 + j3.2 | 0.7 + j2.9 |
| 520 | 0.7 + j3.0 | 0.6 + j3.0 |

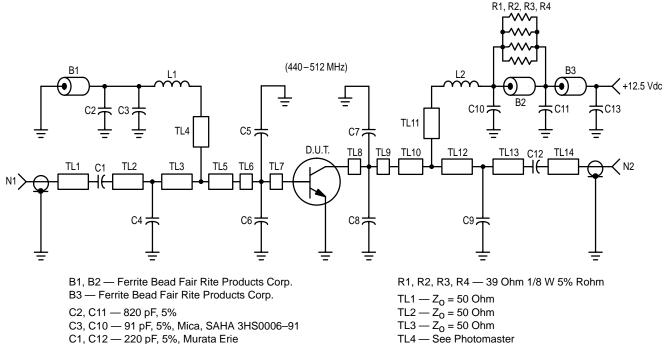
NOTE: Z_{in} & Z_{OL}^* are given from base–to–base and collector–to–collector respectively.



Z_{OL}* = Conjugate of the optimum load impedance into which the device operates at a given output power, voltage and frequency.

Figure 6. Input and Output Impedance Normalized to 10 Ohms Circuit Tuned for Maximum Gain @ $P_0 = 50 \text{ W}$

MOTOROLA RF DEVICE DATA MRF650



C4 — 9.1 pF, 5%, Murata Erie C5, C6, C7, C8 — 43 pF, 5%, Mica SAHA 3HS0006–43 C9 — 10 pF, 5%, Murata Erie C13 — 10 μ F, Electrolytic, 50 V, Panasonic L1 — 7 Turns, 24 AWG, ID Dia. 0.116″

L2 — 5 Turns, 18 AWG, ID Dia. 0.165"

N1, N2 — SMA Flange Mount, Omni–Spectra 2052–1618–02

TL2 — Z_0 = 50 Ohm TL3 — Z_0 = 50 Ohm TL4 — See Photomaster TL5 — Z_0 = 50 Ohm TL6 — See Photomaster TL7 — See Photomaster TL8 — See Photomaster

TL9 — See Photomaster TL10 — $Z_0 = 50$ Ohm TL11 — See Photomaster

TL12 — $Z_0 = 50 \text{ Ohm}$ TL13 — $Z_0 = 50 \text{ Ohm}$ TL14 — $Z_0 = 50 \text{ Ohm}$

Board Material: 1/16" G10, ε_{r} = 4.5 2 oz. Cu Clad Both Sides

Figure 7. Schematic of Broadband Demonstration Amplifier (3)

PERFORMANCE CHARACTERISTICS OF BROADBAND DEMONSTRATION AMPLIFIER

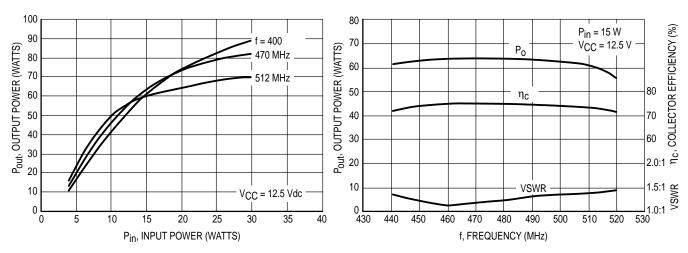
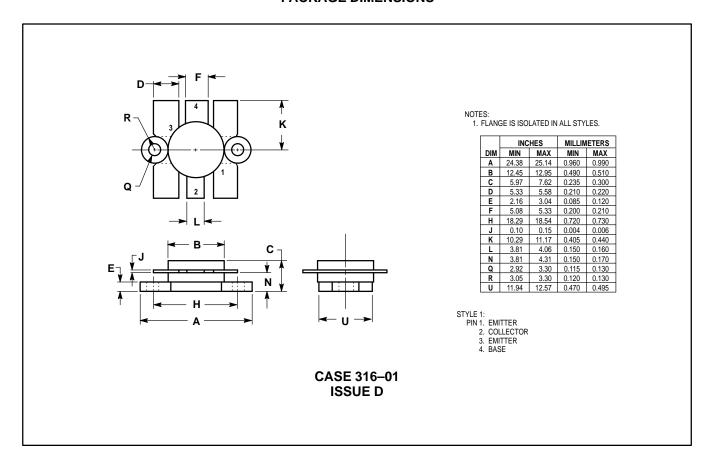


Figure 8. Output Power versus Input Power

Figure 9. P_0 , η_C and VSWR versus Frequency

 $(3) \ Detailed \ design \ and \ performance \ information \ available \ from \ Motorola \ upon \ request.$

PACKAGE DIMENSIONS



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